

SEMICONDUCTOR DICE

PNP SMALL SIGNAL TRANSISTORS

Dice type	V_{CBO}	V_{CEO}	I_{CBO}		h_{FE}				$V_{CE(sat)}$		Max.	f_T	C_{obo}	Chip geometry
	Min.	Min.	Max.	at V_{CB}	at	I_C	V_{CE}	at	I_C	I_B	Min.	Min.	Max.	
	Volts	Volts	nA	Volts	Min.	Max.	mA	Volts	Volts	mA	mA	MHz	pF	
BC556A	80	65	15	30	110	220	2	5	0.3	10	0.5	250*	4.5	G2
BC556B	80	65	15	30	200	450	2	5	0.3	10	0.5	250*	4.5	G2
ZTX504	70	70	200	70	50	300	10	6	0.35	50	5	150	6.0	G2
BCY77A	60†	60	20‡	50†	120	220	2	5	0.25	10	0.25	180*	6.0	G2
BCY77B	60†	60	20‡	50†	180	310	2	5	0.25	10	0.25	180*	6.0	G2
BCY77C	60†	60	20‡	50†	250	460	2	5	0.25	10	0.25	180*	6.0	G2
BC212	60	50	15	30	60	400	2	5	0.07	10	0.5	200	5.0*	G2
BC307	50†	45	100‡	50†	120	460	2	5	0.2	10	0.5	130*	6.0	G2
BC557A	50	45	15	30	110	220	2	5	0.3	10	0.5	250*	4.5	G2
BC557B	50	45	15	30	200	450	2	5	0.3	10	0.5	250*	4.5	G2
BC557C	50	45	15	30	420	800	2	5	0.3	10	0.5	250*	4.5	G2
BC560B	50	45	15	30	200	450	2	5	0.25	10	0.5	250*	4.5	G2
BC560C	50	45	15	30	420	800	2	5	0.25	10	0.5	250*	4.5	G2
BCY79A	45†	45	20‡	35†	120	220	2	5	0.25	10	0.25	180*	6.0	G2
BCY79B	45†	45	20‡	35†	180	310	2	5	0.25	10	0.25	180*	6.0	G2
BCY79C	45†	45	20‡	35†	250	460	2	5	0.25	10	0.25	180*	6.0	G2
ZTX503	45	45	200	45	50	300	10	6	0.35	50	5	150	6.0	G2
BC213	45	30	15	30	80	600	2	5	0.07	10	0.5	200	5.0*	G2
BC214	45	30	15	30	200	600	2	5	0.07	10	0.5	200	5.0*	G2
ZTX502	35	35	200	35	100	300	10	6	0.25	50	5	150	6.0	G2
ZTX501	35	35	200	35	50	300	10	6	0.25	50	5	150	6.0	G2
BCY78A	32†	32	20‡	25†	120	220	2	5	0.25	10	0.25	180*	6.0	G2
BCY78B	32†	32	20‡	25†	180	310	2	5	0.25	10	0.25	180*	6.0	G2
BCY78C	32†	32	20‡	25†	250	460	2	5	0.25	10	0.25	180*	6.0	G2
BCY78D	32†	32	20‡	25†	380	630	2	5	0.25	10	0.25	180*	6.0	G2
BC558A	30	30	15	30	110	220	2	5	0.3	10	0.5	250*	4.5	G2
BC558B	30	30	15	30	200	450	2	5	0.3	10	0.5	250*	4.5	G2
BC558C	30	30	15	30	420	800	2	5	0.3	10	0.5	250*	4.5	G2
BC559B	30	30	15	30	200	450	2	5	0.25	10	0.5	250*	4.5	G2
BC559C	30	30	15	30	420	800	2	5	0.25	10	0.5	250*	4.5	G2
ZTX500	25	25	200	25	50	300	10	6	0.35	50	5	150	6.0	G2

† V_{CES} § I_{CES} *Typical values